MSKSEMI















ESD

TVS

TSS

MOV

GDT

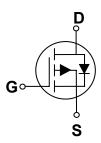
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Broduct data sheet





SOT-23-3L



Features

- $-20V, -3.3A, RDS(ON) = 30m\Omega@VGS = -4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

| BVDSS | RDSON | ID |
|-------|---------------------|-------|
| -20V | $60 \text{m}\Omega$ | -3.3A |

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

| Symbol | Parameter | Rating | Units |
|------------------|---|------------|-------|
| V _D s | Drain-Source Voltage | -20 | V |
| Vgs | Gate-Source Voltage | ±12 | V |
| | Drain Current – Continuous (T _C =250) | -3.3 | А |
| lD | Drain Current – Continuous (T _C =100C) | -2.5 | А |
| I _{DM} | Drain Current – Pulsed ¹ | -13.2 | A |
| D | Power Dissipation (T _C =25C) | 1.56 | W |
| P_D | Power Dissipation – Derate above 250 | 0.012 | W/ C |
| T _{STG} | Storage Temperature Range | -55 to 150 | С |
| TJ | Operating Junction Temperature Range | -55 to 150 | С |

Thermal Ch aracteristics

| Symbol | Parameter | Тур. | Max. | Unit |
|--------|--|------|------|------|
| ReJA | Thermal Resistance Junction to ambient | | 80 | C/ W |











Off Characteristics

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|---|---|--|------|-------|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V , I _D =-250uA | -20 | | | V |
| $\triangle BV_{DSS}/\triangle T_{J}$ | BV _{DSS} Temperature Coefficient | Reference to 250 , I _D =-1mA | | -0.01 | | V/ C |
| | Duain Course Leeks as Current | V _{DS} =-20V , V _{GS} =0V , T _J =250 | | | -1 | uA |
| I _{DSS} Drain-Source Leakage Current | | V _{DS} =-16V , V _{GS} =0V , T _J =125C | | | -10 | uA |
| I _{GSS} | Gate-Source Leakage Current | $V_{GS=} \pm 12V$, $V_{DS}=0V$ | | | ±10 | uA |

On Characteristics

| R _{DS(ON)} | RDS(ON) Static Drain-Source On-Resistance | V _{GS} =-4.5V , I _D =-3A | | 60 | 90 | mΩ | |
|------------------------|---|--|------|------|------|-------|--|
| 1 450(014) | Static Brain-Source On-Resistance | V _{GS} =-2.5V , I _D =-2A | | 90 | 120 | 11122 | |
| V _{GS(th)} | Gate Threshold Voltage |)/ | -0.4 | -0.7 | -1.2 | V | |
| $\triangle V_{GS(th)}$ | V _{GS(th)} Temperature Coefficient | $V_{GS}=V_{DS}$, $I_D=-250uA$ | | 3 | | mV/ C | |
| gfs | Forward Transconductance | V _{DS} =-10V , I _S =-1A | | 2.2 | | S | |

Dynamic and switching Characteristics

| Qg | Total Gate Charge ^{2, 3} | | | 4.8 | |
|---------------------|------------------------------------|---|---|------|---------|
| Qgs | Gate-Source Charge ^{2, 3} | V_{DS} =-10V , V_{GS} =-4.5V , I_{D} =-3A | | 0.5 | nC |
| Q_{gd} | Gate-Drain Charge ^{2, 3} | | 1 | 1.9 | |
| T _{d(on)} | Turn-On Delay Time ^{2,3} | | 1 | 3.5 | |
| Tr | Rise Time ^{2,3} | V_{DD} =-10V , V_{GS} =-4.5V , R_{G} =25 Ω | | 12.6 | . 0 |
| T _{d(off)} | Turn-Off Delay Time ^{2,3} | I _D =-1A | | 32.6 | nS |
| Tf | Fall Time ^{2, 3} | | | 8.4 | |
| Ciss | Input Capacitance | | | 550 | |
| Coss | Output Capacitance | V _{DS} =-10V , V _{GS} =0V , F=1MHz | | 65 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 55 | |

Drain-Source Diode Characteristics and Maximum Ratings

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|--------|---------------------------|---|------|------|------|------|
| ls | Continuous Source Current | \/ =\/ =0\/ Force Current | | | -3.3 | Α |
| lsм | Pulsed Source Current | $V_G=V_D=0V$, Force Current | | | -6.6 | Α |
| VsD | Diode Forward Voltage | V _{GS} =0V , I _S =-1A , T _J =250 | | | -1.2 | V |

Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width ≤ 300 us , duty cycle $\leq 2\%$.
- 3. Essentially independent of operating temperature.



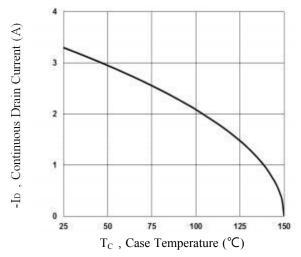


Fig.1 Continuous Drain Current vs. T_c

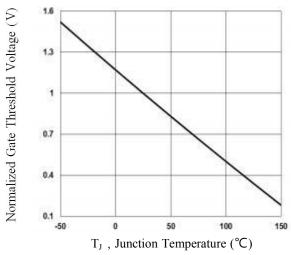
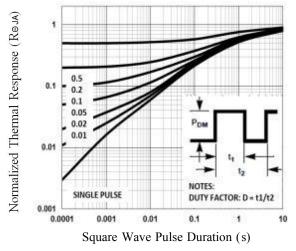
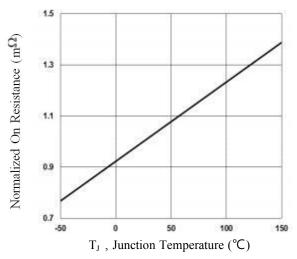


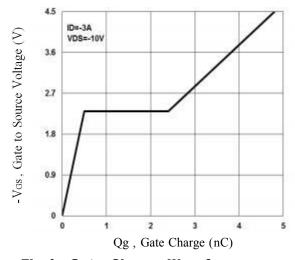
Fig.3 Normalized V_{th} vs. T_J



Normalized Transient Response



Normalized RDSON vs. T_J Fig.2



Gate Charge Waveform

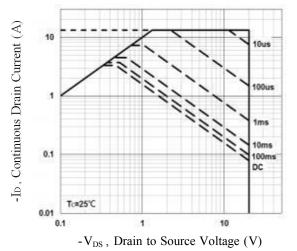
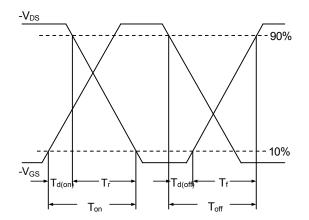


Fig.6 Maximum Safe Operation Area





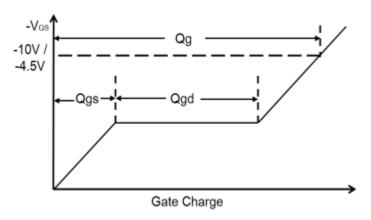


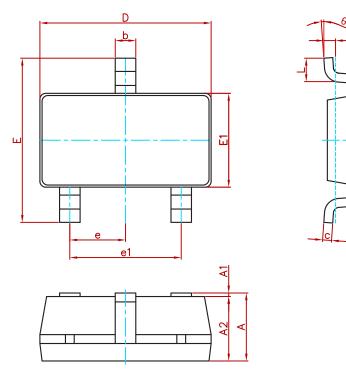
Fig. 7 Switching Time Waveform

Fig. 8 Gate Charge Waveform



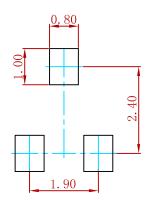
0.200

PACKAGE MECHANICAL DATA



| Symbol | Dimensions In Millimeters | | Dimension | s In Inches |
|--------|---------------------------|-------|-----------|-------------|
| Symbol | Min. | Max. | Min. | Max. |
| Α | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| С | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E1 | 1.500 | 1.700 | 0.059 | 0.067 |
| E | 2.650 | 2.950 | 0.104 | 0.116 |
| е | 0.950(| BSC) | 0.037(| (BSC) |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|--------|-----------|------|
| AO3419 | SOT-23-3L | 3000 |



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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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